

**RRQ020P03** 

## Pch -30V -2A Small Signal MOSFET

## Datasheet

V <sub>DSS</sub>	-30V
R <sub>DS(on)</sub> (Max.)	160mΩ
I <sub>D</sub>	±2A
P <sub>D</sub>	1.25W

## Features

- 1) Low on resistance.
- 2) High Power small mold Package (TSMT6).
- 3) Pb-free lead plating ; RoHS compliant.

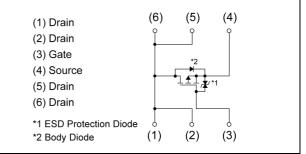
4) Halogen Free.

Application

Switching

●Outline	
SOT-457T	
TSMT6	

#### ●Inner circuit



## Packaging specifications

Туре	Packing	Embossed Tape
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3000
	Taping code	TR
	Marking	UJ

## • Absolute maximum ratings (T<sub>a</sub> = 25°C ,unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V <sub>DSS</sub>	-30	V
Continuous drain current	Ι <sub>D</sub>	±2	А
Pulsed drain current	I <sub>DP</sub> *1	±6	А
Gate - Source voltage	V <sub>GSS</sub>	±20	V
Device discipation	P <sub>D</sub> *2	1.25	W
Power dissipation	P <sub>D</sub> *3	0.95	W
Junction temperature	Tj	150	°C
Operating junction and storage temperature range	T <sub>stg</sub>	-55 to +150	C°

#### •Thermal resistance

Deremeter	Symbol	Values			Linit
Parameter	Symbol	Min.	Тур.	Max.	Unit
Thermal resistance is notion empiont	$R_{thJA}^{*2}$	-	-	100	°C/W
Thermal resistance, junction - ambient	$R_{thJA}^{*3}$	-	-	132	°C/W

## •Electrical characteristics (T<sub>a</sub> = 25°C)

Deremeter	Currence of	Symbol Conditions		Values			
Parameter	Symbol Conditions		Min.	Тур.	Max.	Unit	
Drain - Source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -1mA	-30	-	-	V	
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	I <sub>D</sub> = -1mA referenced to 25°C	-	-24.1	-	mV/°C	
Zero gate voltage drain current	I <sub>DSS</sub>	$I_{DSS}$ $V_{DS}$ = -30V, $V_{GS}$ = 0V		-	-1	μA	
Gate - Source leakage current	ate - Source leakage current $I_{GSS}$ $V_{GS}$ = ±20V, $V_{DS}$ = 0V		-	-	±10	μA	
Gate threshold voltage	$V_{GS(th)}$	$V_{GS(th)}$ $V_{DS} = -10V, I_D = -1mA$		-	-2.5	V	
Gate threshold voltage temperature coefficient $\Delta V_{GS(tr)}$ $\Delta T_i$		I <sub>D</sub> = -1mA referenced to 25°C	-	3.3	-	mV/°C	
		V <sub>GS</sub> = -10V, I <sub>D</sub> = -2.0A	-	115	160		
Static drain - source on - state resistance	R <sub>DS(on)</sub> *4	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -1.0A	-	170	240	mΩ	
		V <sub>GS</sub> = -4.0V, I <sub>D</sub> = -1.0A	-	190	270		
Gate resistance	R <sub>G</sub>	R <sub>G</sub> f = 1MHz, open drain		20	-	Ω	
Forward Transfer Admittance	Y <sub>fs</sub>   <sup>*4</sup>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -2.0A	1.5	-	-	S	

\*1 Pw  $\leq$  10µs, Duty cycle  $\leq$  1%

- \*2 Mounted on a ceramic boad (30×30×0.8mm)
- \*3 Mounted on a FR4 (25×25×0.8mm,Cu pad:625mm<sup>2</sup>)
- \*4 Pulsed



## •Electrical characteristics (T<sub>a</sub> = 25°C)

Deremeter	Sumpleal	Conditions	Values			Linit
Parameter	Symbol	Symbol Conditions		Тур.	Max.	Unit
Input capacitance	C <sub>iss</sub>	iss V <sub>GS</sub> = 0V		230	-	
Output capacitance	C <sub>oss</sub> V <sub>DS</sub> = -10V		-	40	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	C <sub>rss</sub> f = 1MHz		33	-	
Turn - on delay time	t <sub>d(on)</sub> *4	$t_{d(on)}^{*4}$ V <sub>DD</sub> ~ -15V, V <sub>GS</sub> = -10V		13	-	
Rise time	t <sub>r</sub> *4	I <sub>D</sub> = -1.0A	-	15	-	20
Turn - off delay time	$t_{d(off)}^{*4}$	$R_L \simeq 15\Omega$	-	40	-	ns
Fall time	$t_{f}^{*4}$	R <sub>G</sub> = 10Ω	-	20	-	

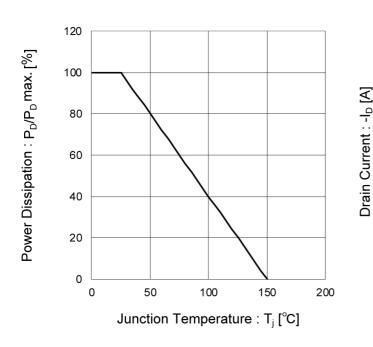
## • Gate charge characteristics ( $T_a = 25^{\circ}C$ )

Parameter	Symbol	Conditions	Values			Unit	
	Symbol Conditions		Min.	Тур.	Max.	Unit	
Total gate charge	$Q_g^{*4}$	V <sub>DD</sub> ≃ -15V,	-	3.2	-		
Gate - Source charge	Q <sub>gs</sub> *4	I <sub>D</sub> = -2.0A,	-	1.2	-	nC	
Gate - Drain charge	${\sf Q}_{\sf gd}{}^{*4}$	V <sub>GS</sub> = -5V	-	0.7	-		

## •Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

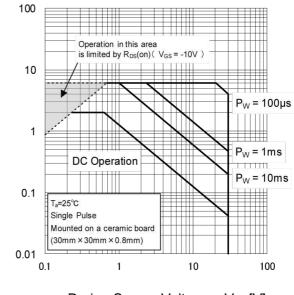
Parameter	Symbol	Conditions	Values			Unit
	Symbol	Conditions	Min.	Тур.	Max.	Unit
Continuous forward current	۱ <sub>s</sub>	T - 25°0	-	-	-1	А
Pulse forward current	I <sub>SP</sub> *1	T <sub>a</sub> = 25°C	-	-	-6	А
Forward voltage	$V_{SD}^{*4}$	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A	-	-	-1.2	V





#### Fig.1 Power Dissipation Derating Curve

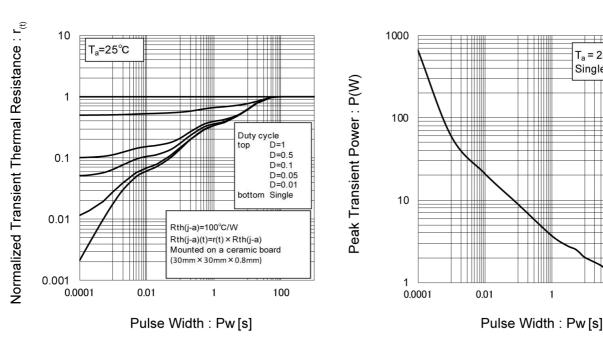
Fig.2 Maximum Safe Operating Area



Drain - Source Voltage : -V<sub>DS</sub> [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

# Fig.4 Single Pulse Maximum Power dissipation



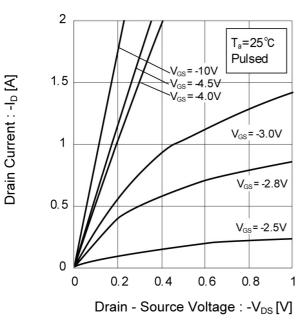
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T<sub>a</sub> = 25°C Single Pulse

+##

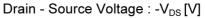
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## Fig.5 Typical Output Characteristics(I)

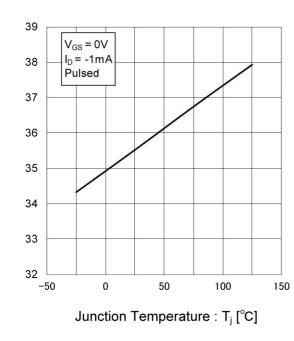
#### 2 = -10V √<sub>GS</sub>= -4.5V $V_{GS}$ = -4.0V '<sub>GS</sub>= -3.0V 1.5 Drain Current : -I<sub>D</sub> [A] V<sub>GS</sub>= -2.8V 1 V<sub>GS</sub>= -2.5V 0.5 T₂=25℃ Pulsed 0 2 0 4 6 8 10

#### Fig.6 Typical Output Characteristics(II)

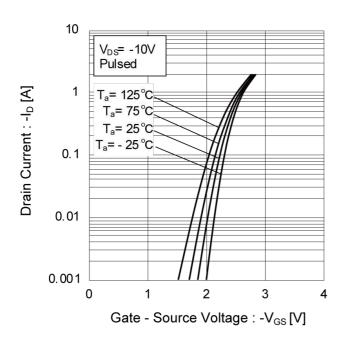


## Fig.7 Breakdown Voltage vs. Junction Temperature

Drain-Source Breakdown Voltage : -V<sub>(BR)DSS</sub> [V]

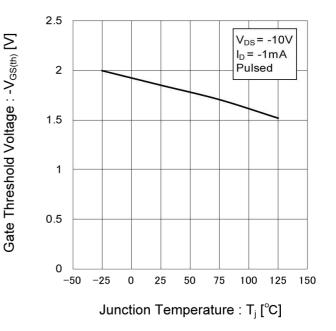




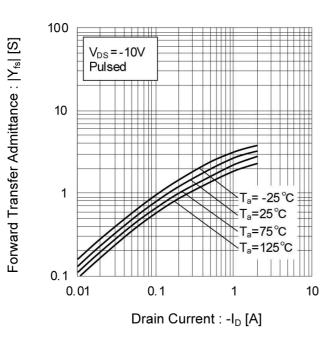


## Fig.8 Typical Transfer Characteristics

Fig.9 Gate Threshold Voltage vs. Junction Temperature



# Fig.10 Forward Transfer Admittance vs. Drain Current





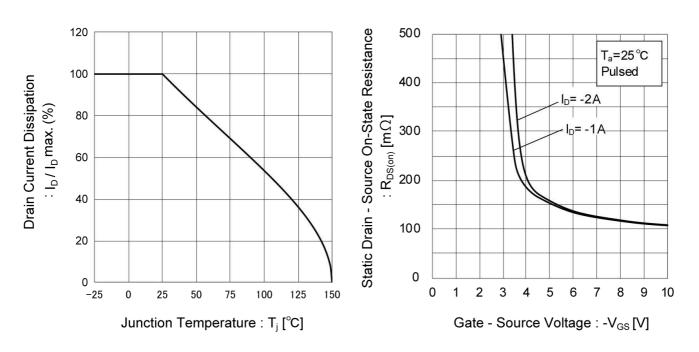


Fig.11 Drain Current Derating Curve

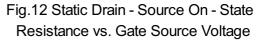
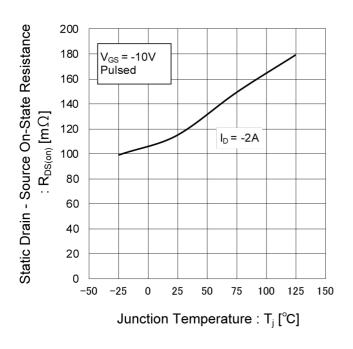


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature





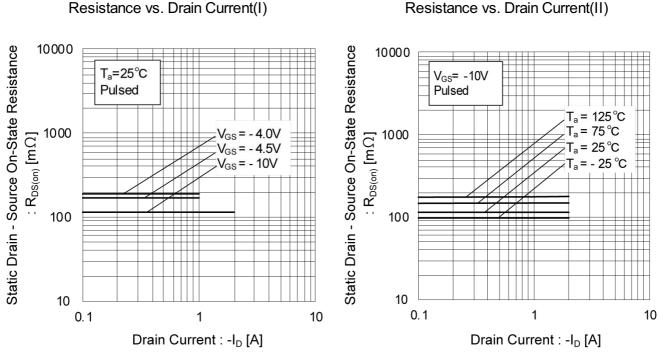


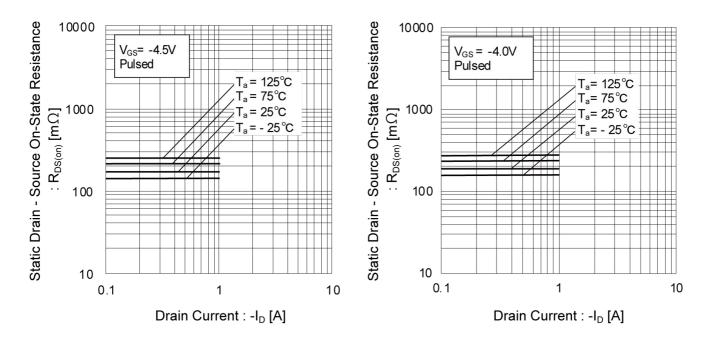
Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I)

Fig.16 Static Drain - Source On - State

Resistance vs. Drain Current(III)

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV)

Fig.15 Static Drain - Source On - State





Source Voltage

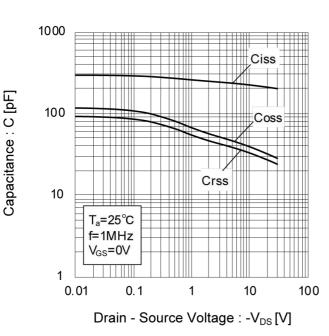


Fig.18 Typical Capacitance vs. Drain -

## 1000 T<sub>a</sub>=25°C V<sub>DD</sub>= -15V V<sub>GS</sub>= -10V $R_G = 10\Omega$ 100 Pulsed t<sub>d(off</sub> 10 t<sub>d(on)</sub> 1 0.01 0.1 1 10

Switching Time : t [ns]

## Fig.19 Switching Characteristics

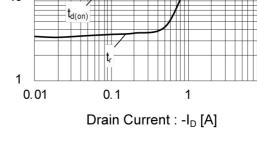


Fig.20 Dynamic Input Characteristics

Gate - Source Voltage : V<sub>GS</sub> [V]

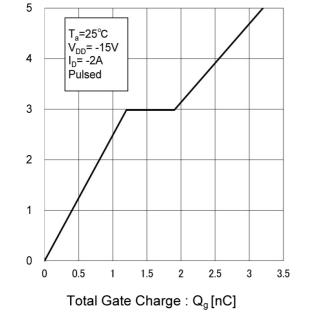
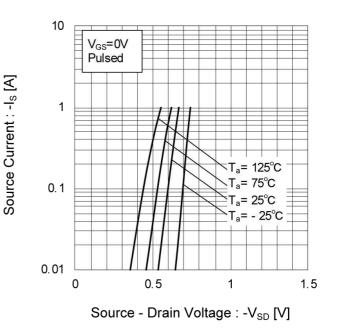


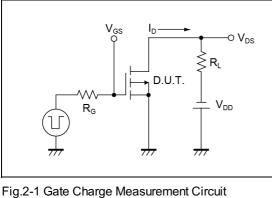
Fig.21 Source Current vs. Source Drain Voltage





#### Measurement circuits





1 1g.2-1 Gale Charge Measurement Circuit

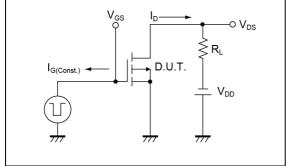
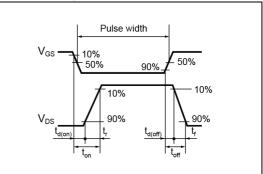
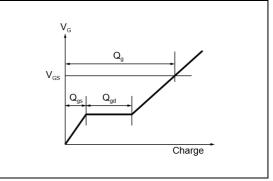


Fig.1-2 Switching Waveforms





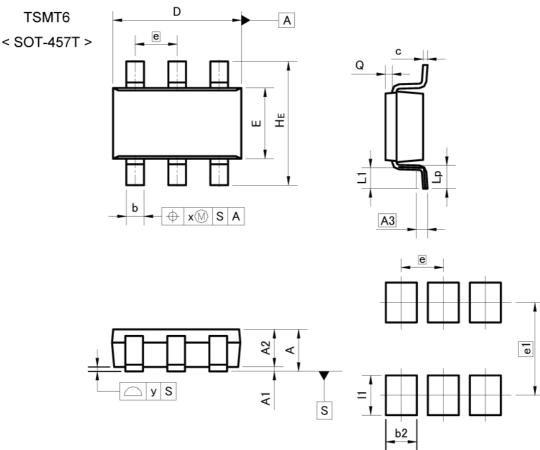


## Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.



#### Dimensions



Pattern of terminal position areas [Not a pattern of soldering pads]

DIM	MILIM	ETERS	INC	HES
	MIN	MAX	MIN	MAX
A	22 <b></b> -	1.00	-	0.039
A1	0.00	0.10	0.000	0.004
A2	0.75	0.95	0.030	0.037
A3	0.	25	0.0	10
b	0.35	0.50	0.014	0.020
С	0.10	0.26	0.004	0.010
D	2.80	3.00	0.110	0.118
E	1.50	1.80	0.059	0.071
е	0.95		0.037	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.05	0.25	0.002	0.010
x	(1 <del>7)</del>	0.20		0.008
у	-	0.10	-	0.004
	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
b2		0.70		0.028
e1	2.10		0.0	83

Dimension in mm/inches

-

11

0.90

-



0.035

## Notice

#### Precaution on using ROHM Products

1. Our Products are designed and manufactured for application in ordinary electronic equipments (such as AV equipment, OA equipment, telecommunication equipment, home electronic appliances, amusement equipment, etc.). If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment <sup>(Note 1)</sup>, transport equipment, traffic equipment, aircraft/spacecraft, nuclear power controllers, fuel controllers, car equipment including car accessories, safety devices, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

JAPAN	USA	EU	CHINA
CLASSⅢ	CLASSⅢ	CLASS II b	CLASSII
CLASSⅣ	CLASSIII	CLASSⅢ	CLASSI

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  - [a] Use of our Products in any types of liquid, including water, oils, chemicals, and organic solvents
  - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
  - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

#### Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

#### Precautions Regarding Application Examples and External Circuits

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- 2. You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

#### **Precaution for Electrostatic**

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

#### Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
  - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

#### **Precaution for Product Label**

A two-dimensional barcode printed on ROHM Products label is for ROHM's internal use only.

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When disposing Products please dispose them properly using an authorized industry waste company.

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